

SILICON POWER RECTIFIER

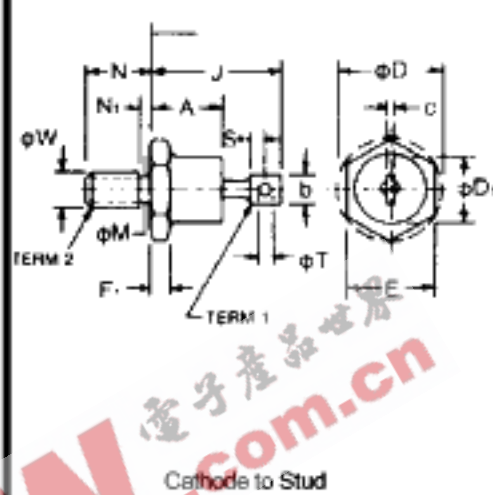
DESCRIPTION:

The **ASI 1N253** is Designed for General Purpose Power Supply Applications.

MAXIMUM RATINGS

I_o	1.0 A @ $T_C = 135\text{ }^\circ\text{C}$
V_{RVM}	100 V
T_J	-65 $^\circ\text{C}$ to +170 $^\circ\text{C}$
T_{STG}	-65 $^\circ\text{C}$ to +175 $^\circ\text{C}$
θ_{JC}	35 $^\circ\text{C/W}$

PACKAGE STYLE DO-4			
SYMBOL	DIMENSIONS		
	INCHES		MILLIMETERS
	MIN.	MAX.	MIN.
A		0.405	
b		0.250	
c			
ϕD		0.505	
ϕD_1	0.265	0.424	6.74
E	0.423	0.438	10.75
F_1	0.075	0.175	1.91
J	0.600	0.800	15.24
ϕM	0.163	0.189	4.15
N	0.422	0.453	10.72
N_1		0.078	
S			
ϕT	0.060	0.095	1.53
ϕW	10-32	UNF-2A	10-32



CHARACTERISTICS $T_J = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UN
I_R	$V_R = 100\text{ V}$ $T_J = 150\text{ }^\circ\text{C}$		10 100	100 1000	
V_F	$I_F = 1.0\text{ A}$			1.2	
I_{FSM}	NON REPETITIVE $t_p = 8.3\text{ ms}$	15			

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